



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C	
30V	2.8Ω @ V _{GS} = 10V	380mA	
30 V	3.8Ω @ $V_{GS} = 5V$	330mA	

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

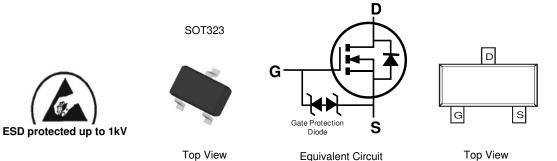
- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 1kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding
 Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (Approximate)



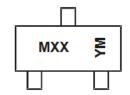
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN63D8LW-7	SOT323	3000/Tape & Reel
DMN63D8LW-13	SOT323	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} \text{MXX=} \underline{P} \text{roduct Type Marking Code} \\ \text{YM} = \overline{D} \text{ate Code Marking} \\ \text{Y or } \overline{\text{Y}} = \text{Year (ex: B} = 2014) \\ \text{M} = \text{Month (ex: 9} = \text{September)} \end{array}$

Date Code Key

Date Odde R	Cy											
Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	E	F	G	Н	I	J	K	L	М
	- -	·	T = ==	· -	I	I -	·	I _	I	_	l	I
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	30	V	
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Dunin Comment (Note C) V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	380 300	mA
Continuous Drain Current (Note 6) V _{GS} = 10V	t<5s	I _D	430 340	mA	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	%) (Note 6))	I _{DM}	1.2	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	426	°C/W
Total Power Dissipation (Note 6)		P _D	420	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	301	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

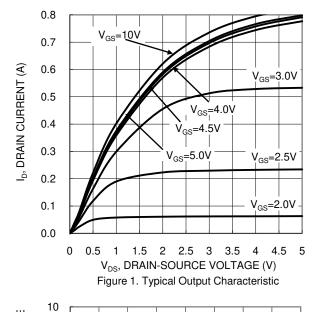
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

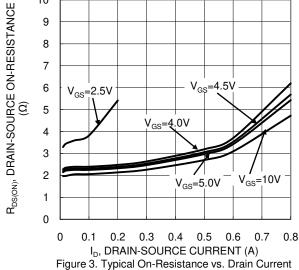
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Cymbol		1,76	Mux	Oiiit	rest condition	
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±10.0	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.8		1.5	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		_		2.8		$V_{GS} = 10.0V, I_D = 250mA$	
				3.8		$V_{GS} = 5.0V, I_D = 250mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_		4.2	Ω	$V_{GS} = 4.5V, I_D = 250mA$	
	, ,	_		4.5		$V_{GS} = 4.0V, I_D = 250mA$	
				13		V _{GS} = 2.5V, I _D = 10mA	
Forward Transconductance	g FS	80		_	mS	V _{DS} = 10V, I _D = 0.115A	
Diode Forward Voltage	V_{SD}		8.0	1.2	٧	V _{GS} = 0V, I _S = 115mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	23.2	_			
Output Capacitance	Coss		3.0	_	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C_{rss}	_	2.2	_			
Gate Resistance	Rg		79.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge V _{GS} = 10V	Q_g	_	0.9	_			
Total Gate Charge V _{GS} = 4.5V	Qg	_	0.4	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$	
Gate-Source Charge	Q _{gs}		0.1	_	IIC	$I_D = 150 \text{mA}$	
Gate-Drain Charge	Q_{gd}		0.2	_			
Turn-On Delay Time	t _{D(ON)}		2.3	_			
Turn-On Rise Time	t _R		3.9	_		$V_{DD} = 30V, I_D = 0.115A, V_{GEN} = 10V$	
Turn-Off Delay Time	t _{D(OFF)}		11.4	_	ns	$R_{GEN} = 25\Omega$	
Turn-Off Fall Time	t _F	_	16.7	_			

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

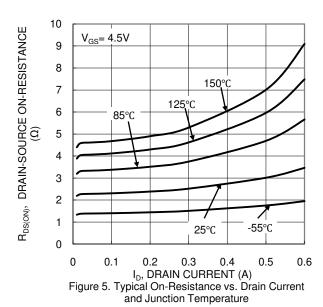
- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

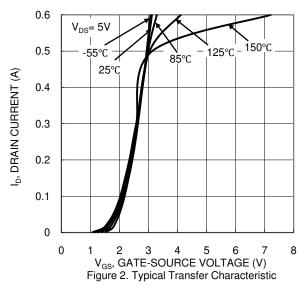


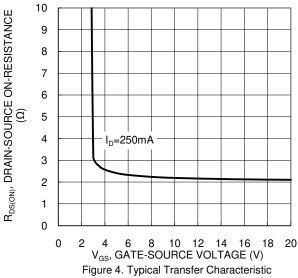




and Gate Voltage







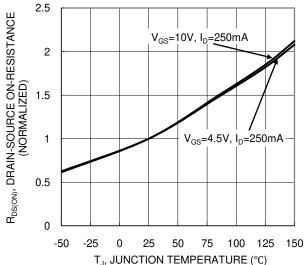


Figure 6. On-Resistance Variation with Junction Temperature



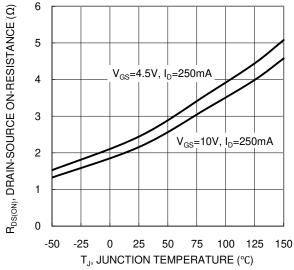
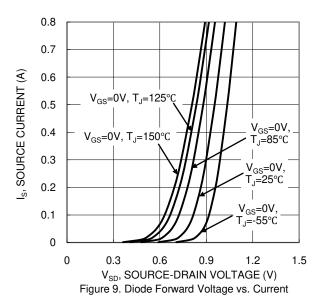


Figure 7. On-Resistance Variation with Junction Temperature



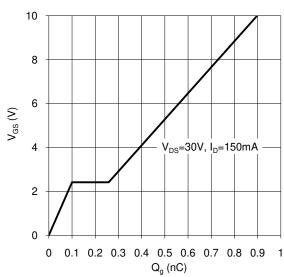


Figure 11. Gate Charge

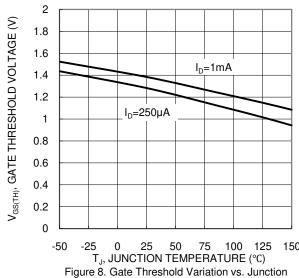
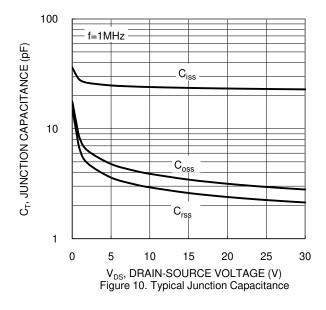
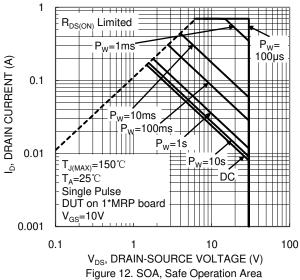


Figure 8. Gate Threshold Variation vs. Junction Temperature







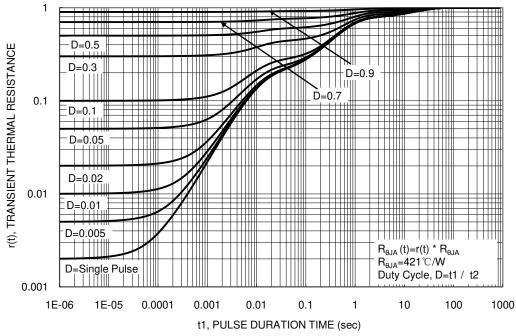
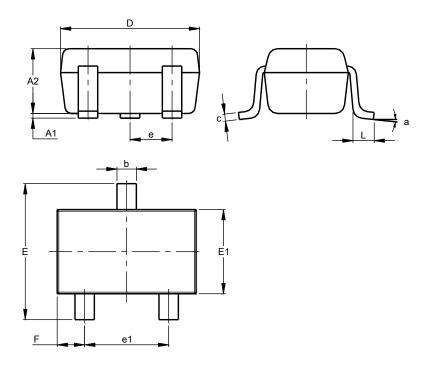


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

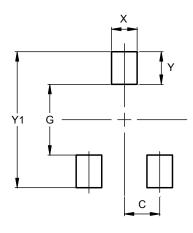


SOT323								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
С	0.10	0.18	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	().650 E	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	8°							
All	All Dimensions in mm							



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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